

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,427,555 B2
APPLICATION NO. : 10/537385
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INVENTOR(S) : Haskell et al.

Page 1 of 1

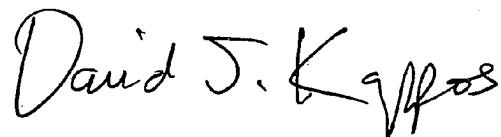
It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, Item (56) Other Pubs. Page 4:

Please insert --GU, S. et al., "The Impact of initial growth and substrate nitridation on thick GaN growth on sapphire by hidride vapor phase epitaxy", Journal of Crystal Growth, North-Holland Publishing, Amsterdam, NL, vol. 231, no. 3, October 2001 (2001-10), pages 342-351--.

Signed and Sealed this

Second Day of November, 2010



David J. Kappos
Director of the United States Patent and Trademark Office